amgj [illegible]

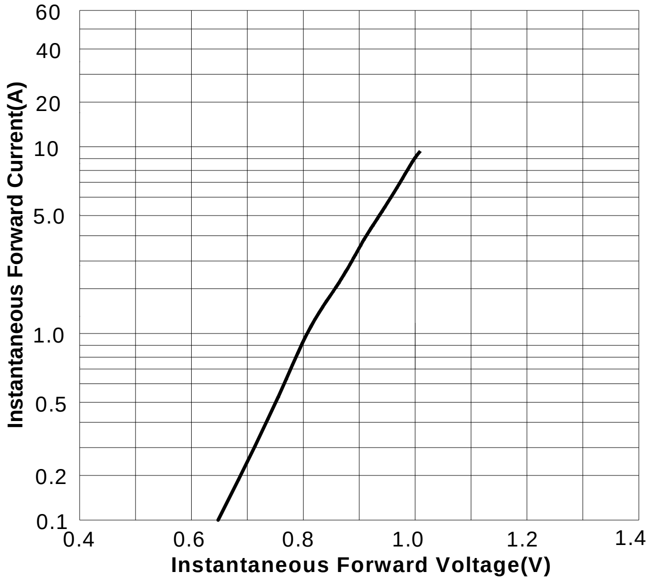
■Electrical Characteristics Ta=25 Unless otherwise specified

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	RYBSN10010
Maximum reverse recovery time	t_{rr}	ns	I_F=0.5A,I_R=1.0A, I_{rr}=0.25A	500
Maximum instantaneous forward voltage drop per diode	V_F	V	I_{FM}=5.0A	1.3
Maximum DC reverse current at rated DC blocking voltage per diode	I_R	μA	Tj =25	5
			Tj =125	100
Typical junction capacitance	Cj	pF	Measured at 1MHz and Applied Reverse Voltage of 4.0 V.D.C	75

■Thermal Characteristics Ta=25 Unless otherwise specified

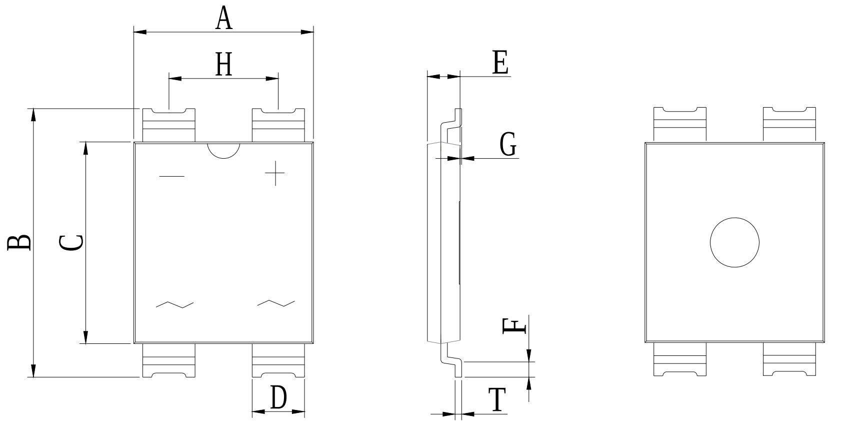
PARAMETER	SYMBOL	

FIG3: Typical Forward Voltage



■ Outline Dimensions

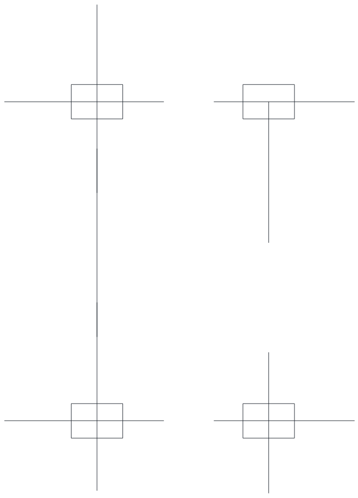
RYBS6



Dimensions in millimeters

YBS6		
Dim	**Min**	**Max**
A	10.70	11.30
B	15.85	16.65
C	11.70	12.30
D	3.05	3.35
E	1.80	2.20
F	0.70	1.10
G	0	0.20
H	6.55	6.85
T	0.35	0.55

■ Suggested pad layout



RYBS6	
Dim	**Min**
P1	15.50
P2	6.70
Q1	1.00
Q2	3.20

Disclaimer

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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety